

Dual N-Channel Power MOSFET

20V, 6.0A, 30mΩ

FEATURES

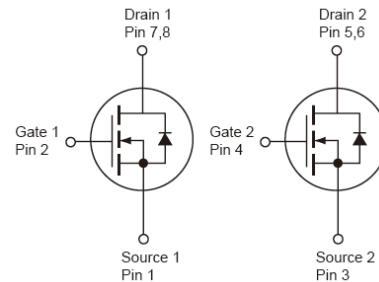
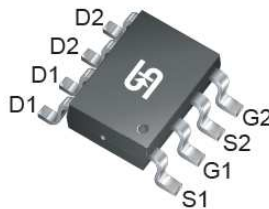
- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

APPLICATION

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

KEY PERFORMANCE PARAMETERS

PARAMETER	VALUE	UNIT
V_{DS}	20	V
$R_{DS(on)}$ (max)	$V_{GS} = 4.5V$	30
	$V_{GS} = 2.5V$	40
Q_g	4.86	nC


SOP-8

Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current (Note 1)	I_D	6	A
Pulsed Drain Current (Note 2)	I_{DM}	30	A
Continuous Source Current (Diode Conduction)	I_S	1.7	A
Total Power Dissipation	P_{DTOT}	$T_A = 25^\circ\text{C}$	1.6
		$T_A = 75^\circ\text{C}$	1.1
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	40	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	77	$^\circ\text{C/W}$

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static ^(Note 3)						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	BV _{DSS}	20	--	--	V
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	V _{GS(TH)}	0.6	--	--	V
Gate Body Leakage	V _{GS} = ±12V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V _{DS} = 20V, V _{GS} = 0V	I _{DSS}	--	--	1	μA
On-State Drain Current	V _{DS} = 5V, V _{GS} = 4.5V	I _{D(ON)}	30	--	--	A
Drain-Source On-State Resistance	V _{GS} = 4.5V, I _D = 6.0A	R _{DS(ON)}	--	21	30	mΩ
	V _{GS} = 2.5V, I _D = 5.2A		--	30	40	
Forward Transconductance	V _{DS} = 10V, I _D = 6A	g _{fs}	--	30	--	S
Dynamic ^(Note 4)						
Total Gate Charge	V _{DS} = 10V, I _D = 6A, V _{GS} = 4.5V	Q _g	--	4.86	--	nC
Gate-Source Charge		Q _{gs}	--	0.92	--	
Gate-Drain Charge		Q _{gd}	--	1.4	--	
Input Capacitance	V _{DS} = 8V, V _{GS} = 0V, F = 1.0MHz	C _{iss}	--	562	--	pF
Output Capacitance		C _{oss}	--	106	--	
Reverse Transfer Capacitance		C _{rss}		75		
Switching ^(Note 5)						
Turn-On Delay Time	V _{DD} = 10V, R _{GEN} = 6Ω, I _D = 1A, V _{GS} = 4.5V,	t _{d(on)}	--	8.1	--	ns
Turn-On Rise Time		t _r	--	9.95	--	
Turn-Off Delay Time		t _{d(off)}	--	21.85	--	
Turn-Off Fall Time		t _f	--	5.35	--	
Source-Drain Diode ^(Note 3)						
Forward Voltage	I _S = 1.7A, V _{GS} = 0V	V _{SD}	--	0.7	1.2	V

Notes:

- Pulse width limited by the Maximum junction temperature.
- Surface Mounted on FR4 Board, $t \leq 5$ sec.
- Pulse test: $PW \leq 300\mu s$, duty cycle $\leq 2\%$.
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM9926DCS RLG	SOP-8	2,500pcs / 13" Reel

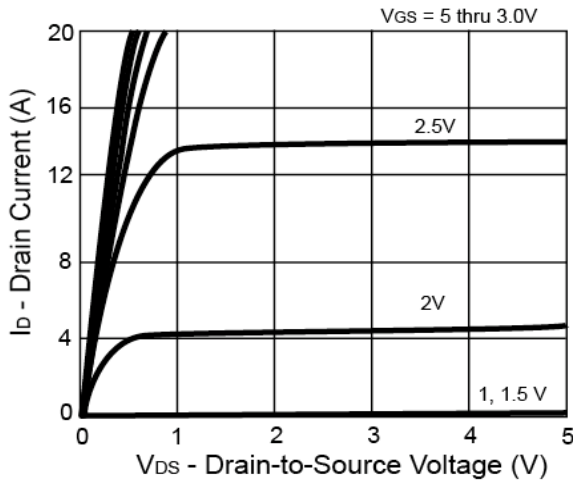
Note:

1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
2. Halogen-free according to IEC 61249-2-21 definition

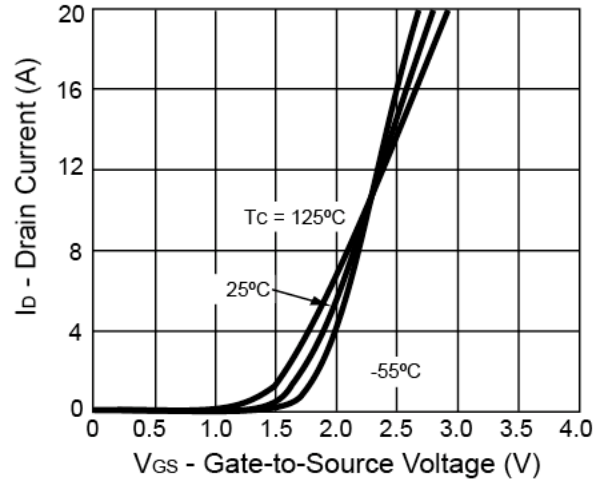
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

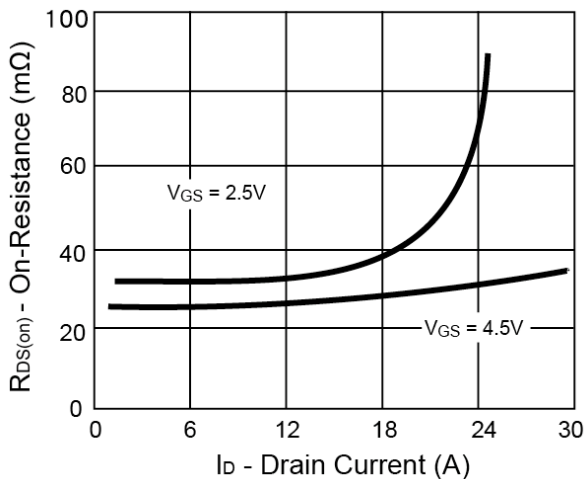
Output Characteristics



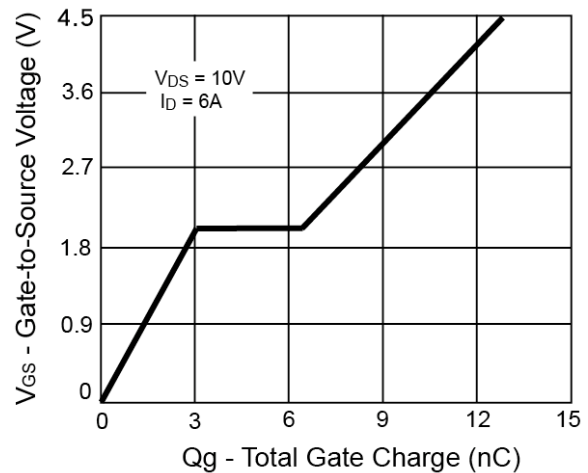
Transfer Characteristics



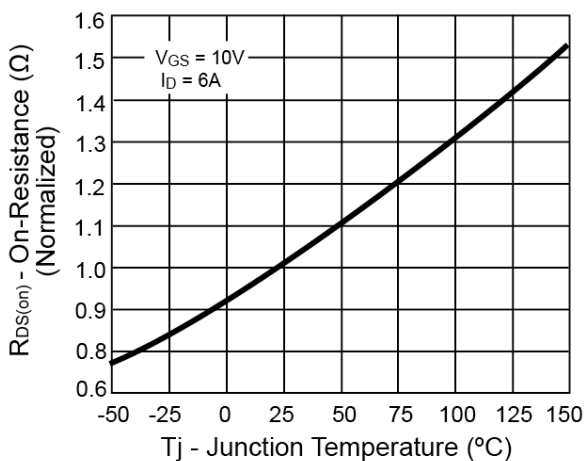
On-Resistance vs. Drain Current



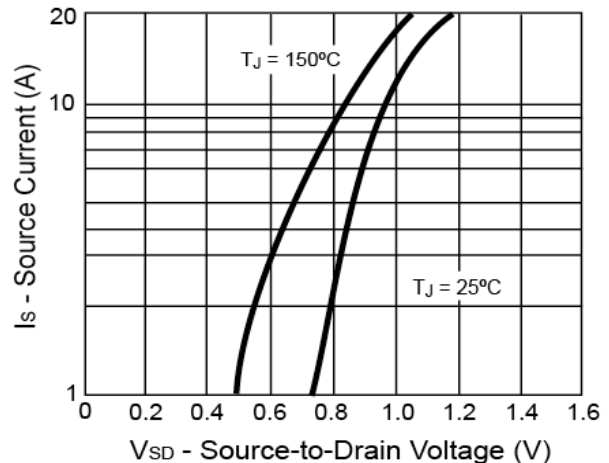
Gate Charge



On-Resistance vs. Junction Temperature



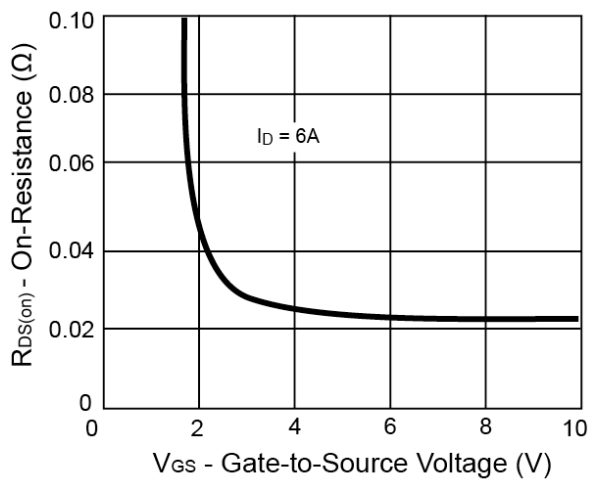
Source-Drain Diode Forward Voltage



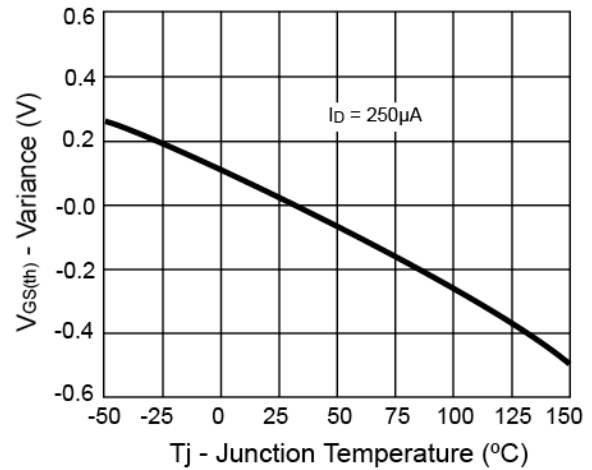
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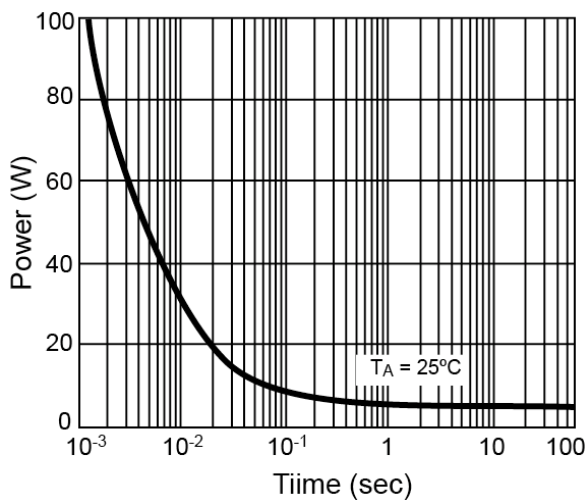
On-Resistance vs. Gate-Source Voltage



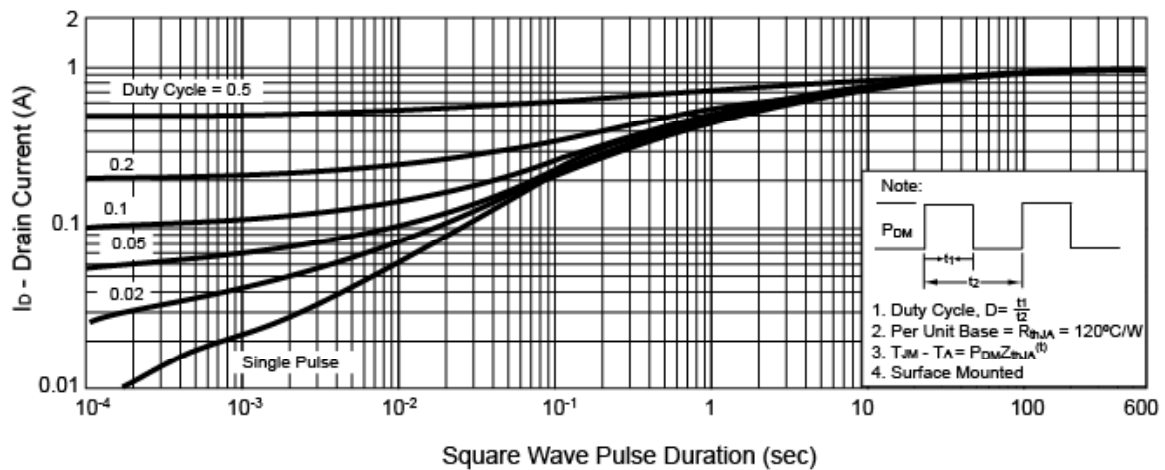
Threshold Voltage



Single Pulse Power

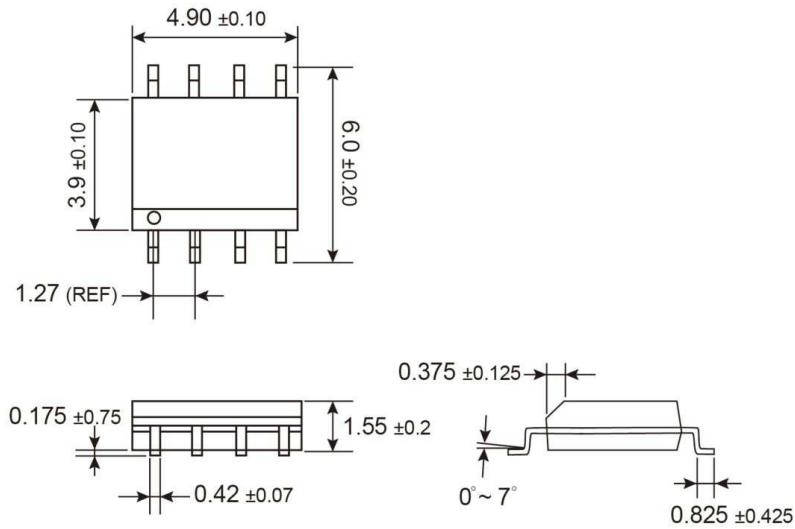


Normalized Thermal Transient Impedance, Junction-to-Ambient

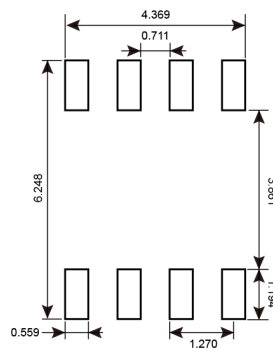


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

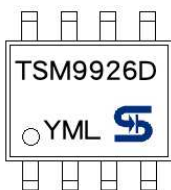
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SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan **P** =Feb **Q** =Mar **R** =Apr

S =May **T** =Jun **U** =Jul **V** =Aug

W =Sep **X** =Oct **Y** =Nov **Z** =Dec

L = Lot Code (1~9, A~Z)

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